**ELIMINATION OF DENDRITE FORMATION DURING METAL/** 

**CHALCOGENIDE GLASS DEPOSITION** 

Abstract of the Disclosure

A method of forming a programmable conductor memory cell array is disclosed

wherein metal and chalcogenide glass are co-sputtered to fill an array of cell vias in a

prepared substrate. The prepared substrate is heated above room temperature before the

metal and chalcogenide glass film is deposited, and the heating is maintained throughout the

deposition. The resulting metal/chalcogenide glass film has good homogeneity, a desired

ratio of components, and has a regular surface.

W:\DOC\$\ASA\ASA-12083.DOC

50302

L:\DOCS\MSO\MSO-4403.DOC

062303

Micron Ref.: 00-1234.01 -12- MICRON.250C1